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## **AN APPARATUS AND A METHOD FOR FORMING AN ALLOY LAYER OVER A SUBSTRATE**

### **BACKGROUND**

#### **CROSS-REFERENCE TO RELATED APPLICATION**

[0001] This application is a divisional application of U.S. Patent Application <sup>now US Patent 6,638,580,</sup> No. 09/752,492, filed December 29, 2000, titled Apparatus and Method for Forming an Alloy Layer Over a Substrate.

#### **FIELD**

[0002] The invention relates to introducing at least two metals into a chamber and forming a layer over a substrate, and more specifically, to forming an alloy layer over a substrate.

#### **BACKGROUND**

[0003] Integrated circuit structures are generally formed of numerous discrete devices on a semiconductor chip such as a silicon semiconductor chip. The individual devices are interconnected in appropriate patterns to one another and to external devices through the use of interconnection lines or interconnects to form an integrated device. Typically, many integrated circuit devices are formed on a single structure, such as a wafer substrate and, once formed, are separated into individual chips or dies for use in various environments.

[0004] There are several conventional processes for introducing metals such as aluminum, aluminum alloy, or platinum to form an interconnect over a substrate. The metal is generally introduced in the form of a deposition process, (e.g., chemical vapor